

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_A = 25^\circ C$
60V	80m $\Omega$ @ $V_{GS} = 10V$	7.90A
	150m $\Omega$ @ $V_{GS} = 4.5V$	5.75A

## Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- Power management functions

## Features and Benefits

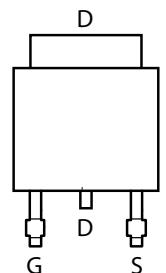
- Low on-resistance
- Fast switching speed
- "Green" component and RoHS compliant (Note 1)

## Mechanical Data

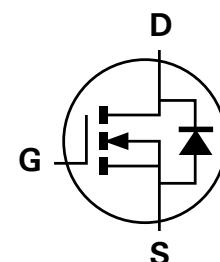
- Case: TO-252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)



TOP VIEW



PIN OUT -TOP VIEW



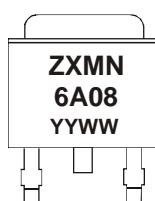
Equivalent Circuit

## Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A08KTC	See Below	13	16	2,500

Note: 1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

## Marking Information



ZXMN = Product Type Marking Code, Line 1  
 6A08 = Product Type Marking Code, Line 2  
 YYWW = Date Code Marking  
 YY = Year (ex: 09 = 2009)  
 WW = Week (01-52)

**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain-Source voltage		$V_{DSS}$	60	V
Gate-Source voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain current	$V_{GS} = 10\text{V}$	$I_D$	7.90	A
			6.30	
			5.36	
Pulsed Drain current	$V_{GS} = 10\text{V}$	$I_{DM}$	24.3	A
Continuous Source current (Body diode)	(Note 3)	$I_S$	9.0	A
Pulsed Source current (Body diode)	(Note 4)	$I_{SM}$	24.3	A

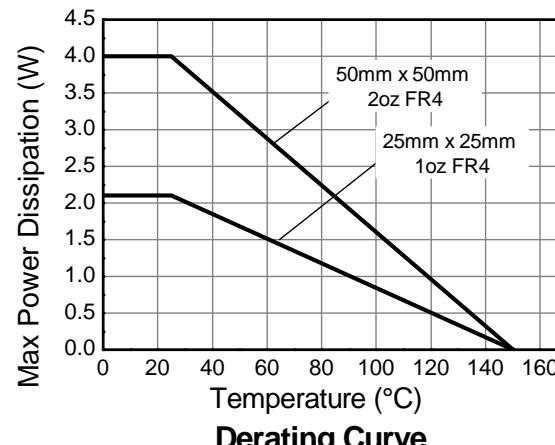
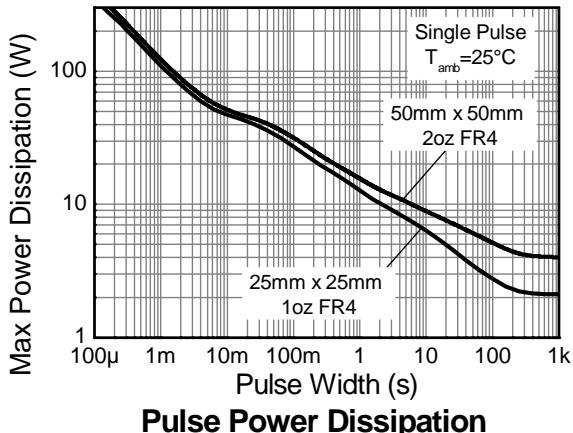
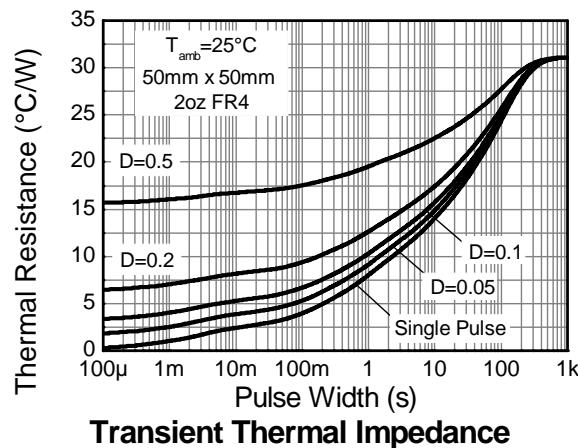
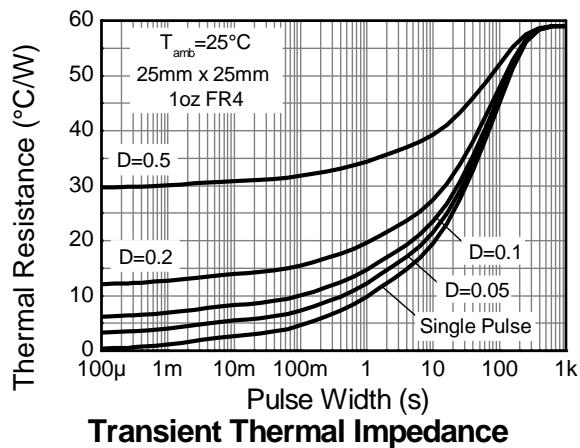
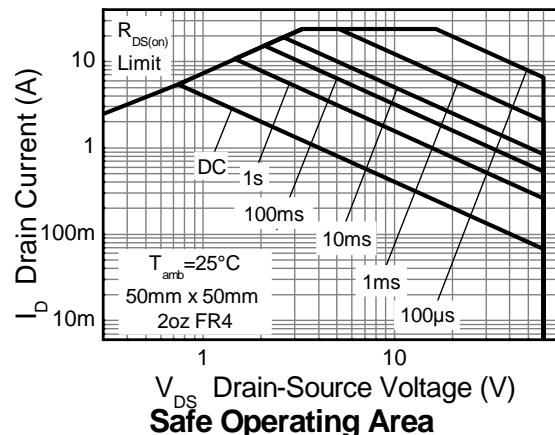
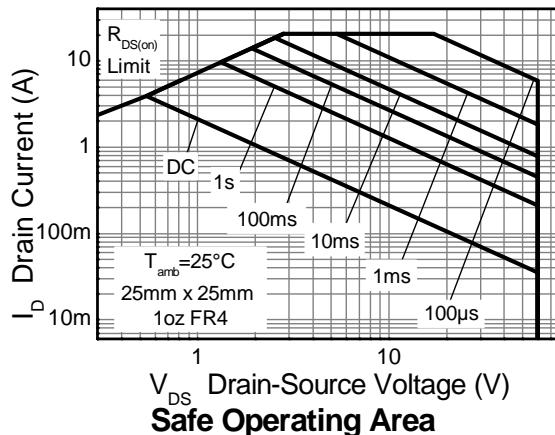
**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation	(Note 2)	$P_D$	4.13	W mW/°C
	(Note 3)		33.0	
	(Note 5)		8.94	
Linear derating factor	(Note 2)	$R_{\theta JA}$	71.5	°C/W
	(Note 3)		2.12	
	(Note 5)		16.9	
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	30.3	°C/W
	(Note 3)		14.0	
	(Note 5)		59.1	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	2.77	
Operating and storage temperature range		$T_J, T_{STG}$	-55 to 150	°C

Notes:

2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
3. Same as note 2, except the device is measured at  $t \leq 10$  sec.
4. Same as note 2, except the device is pulsed with  $D = 0.02$  and pulse width 300  $\mu\text{s}$ . The pulse current is limited by the maximum junction temperature.
5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
6. Thermal resistance from junction to solder-point (at the end of the drain lead).

## Thermal Characteristics



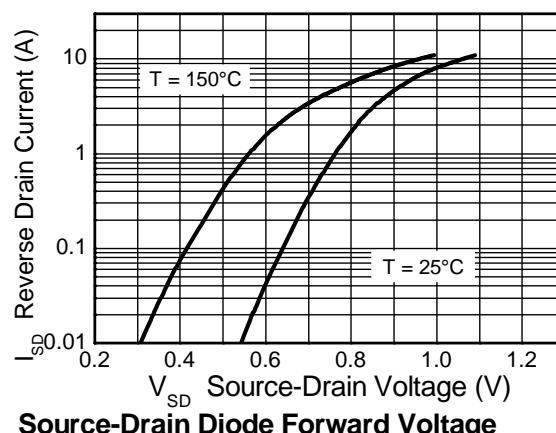
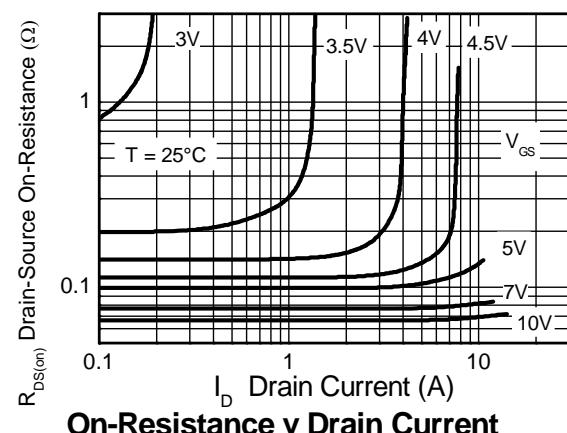
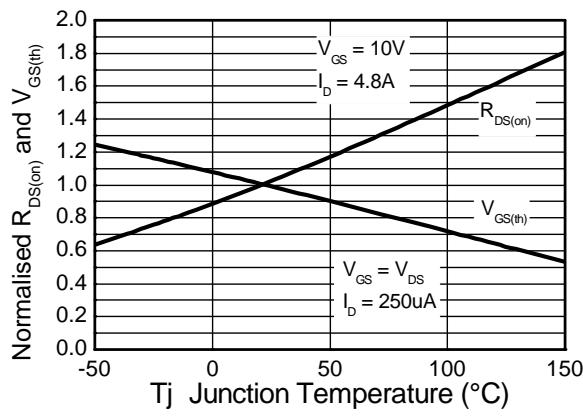
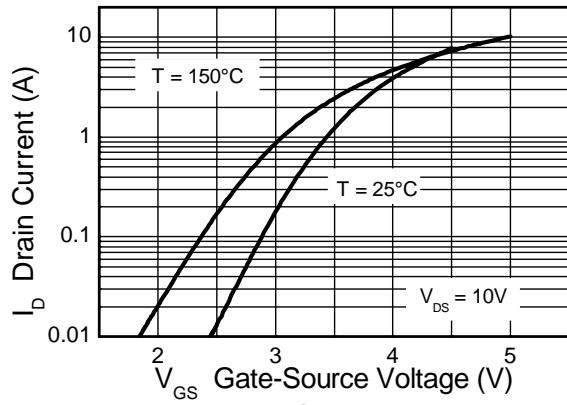
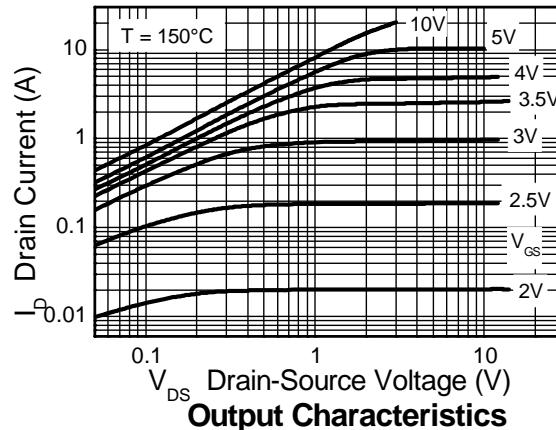
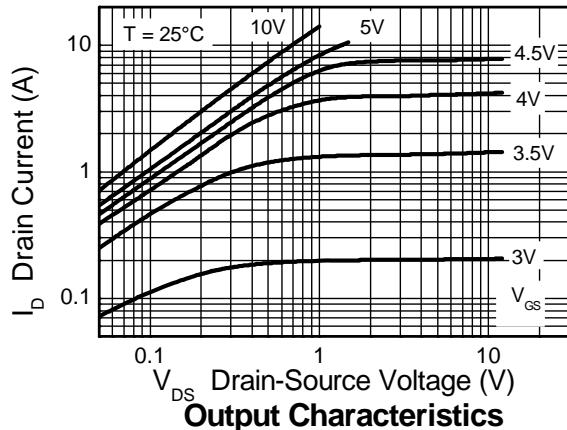
**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	60	—	—	V	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	0.5	$\mu\text{A}$	$V_{DS} = 60\text{V}$ , $V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(\text{th})}$	1.0	—	3.0	V	$I_D = 250\mu\text{A}$ , $V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 7)	$R_{DS(\text{ON})}$	—	—	0.080	$\Omega$	$V_{GS} = 10\text{V}$ , $I_D = 4.8\text{A}$
				0.150		$V_{GS} = 4.5\text{V}$ , $I_D = 4.2\text{A}$
Forward Transconductance (Notes 7 & 8)	$g_{fs}$	—	6.6	—	S	$V_{DS} = 15\text{V}$ , $I_D = 4.8\text{A}$
Diode Forward Voltage (Note 7)	$V_{SD}$	—	0.88	0.95	V	$I_S = 4.0\text{A}$ , $V_{GS} = 0\text{V}$
Reverse recovery time (Note 8)	$t_{rr}$	—	19.2	—	ns	$I_S = 1.4\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge (Note 8)	$Q_{rr}$	—	30.3	—	nC	
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	459	—	pF	$V_{DS} = 40\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	—	44.2	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	24.1	—	pF	
Total Gate Charge	$Q_g$	—	3.8	—	nC	$V_{GS} = 4.5\text{V}$ $V_{GS} = 10\text{V}$ $V_{DS} = 30\text{V}$ $I_D = 1.4\text{A}$
Total Gate Charge	$Q_g$	—	5.8	—	nC	
Gate-Source Charge	$Q_{gs}$	—	1.4	—	nC	
Gate-Drain Charge	$Q_{gd}$	—	1.9	—	nC	
Turn-On Delay Time (Note 9)	$t_{D(\text{on})}$	—	2.6	—	ns	$V_{DD} = 30\text{V}$ , $V_{GS} = 10\text{V}$ $I_D = 1.5\text{A}$ , $R_G \geq 6.0\Omega$
Turn-On Rise Time (Note 9)	$t_r$	—	2.1	—	ns	
Turn-Off Delay Time (Note 9)	$t_{D(\text{off})}$	—	12.3	—	ns	
Turn-Off Fall Time (Note 9)	$t_f$	—	4.6	—	ns	

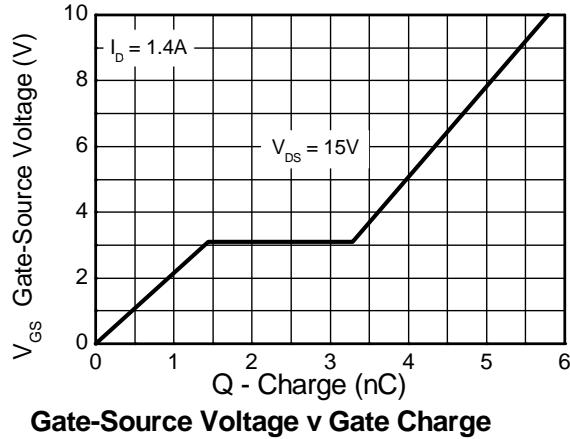
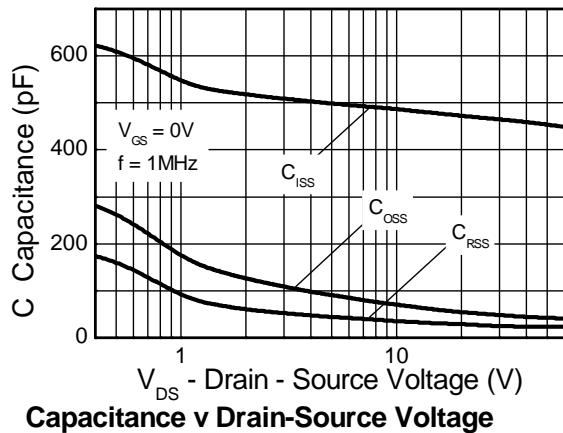
Notes:

7. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$
8. For design aid only, not subject to production testing.
9. Switching characteristics are independent of operating junction temperatures.

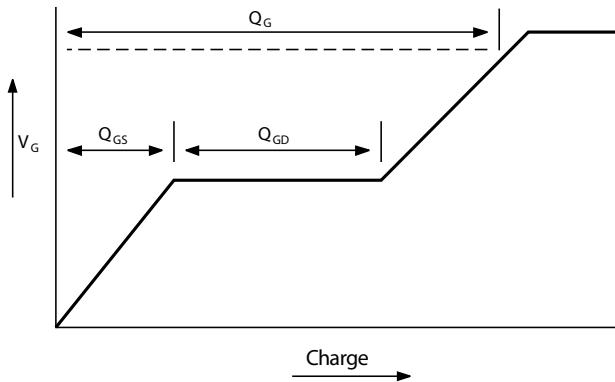
## Typical Characteristics



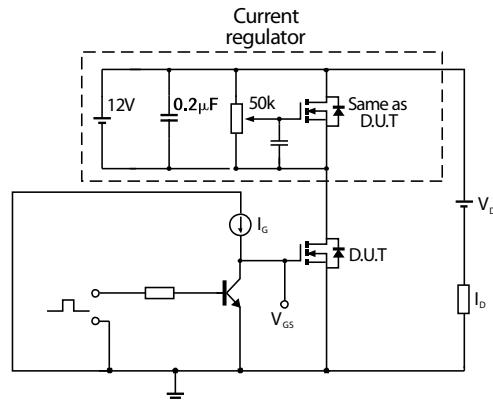
## Typical Characteristics - continued



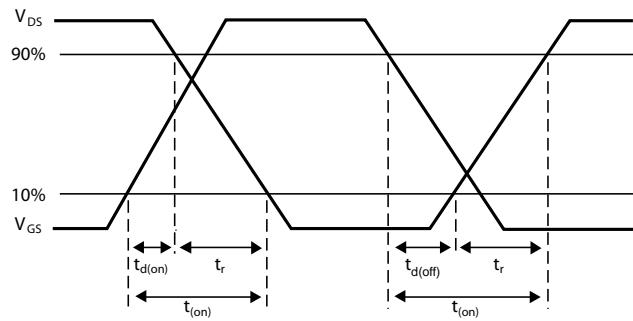
## Test Circuits



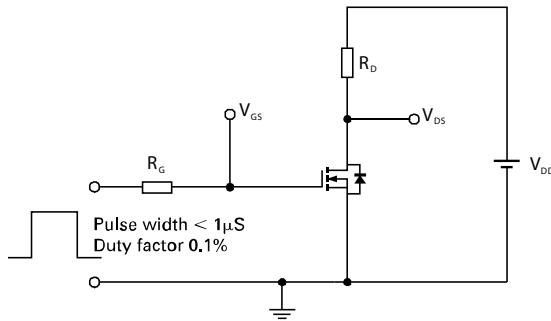
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

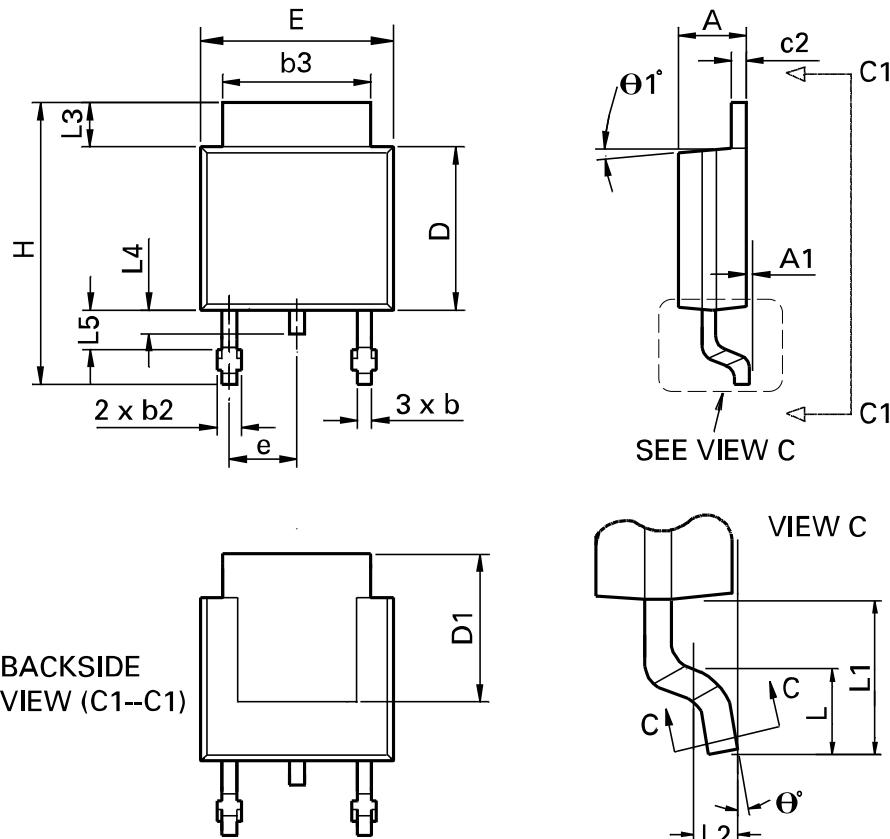


Switching time test circuit

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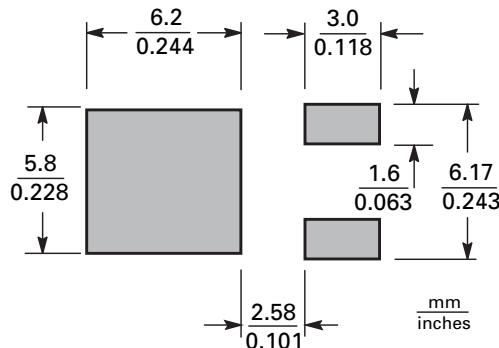
**Package Outline Dimensions**


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DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	theta 1	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	theta	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

## Suggested Pad Layout



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